

### -20V PNP LOW SATURATION TRANSISTOR IN U-DFN2020-3

### Features

- BVCEO > -20V
- hFE Specified up to -6A for High Current Gain Hold Up
- Low Profile 0.6mm High Package for Thin Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotiveproducts/.

• This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

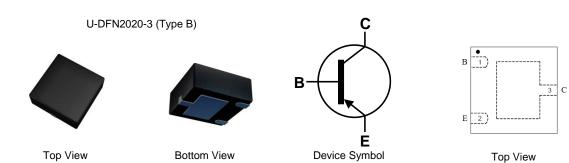
https://www.diodes.com/quality/product-definitions/

### **Mechanical Data**

- Case: U-DFN2020-3 (Type B)
- Nominal Package Height: 0.6mm
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.01 grams (Approximate)

## Applications

- DC-DC Converters
- Charging Circuits
- Motor Control
- Power Switches



Pin-Out

## Ordering Information (Note 4)

	Marking			
Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DXTP5820CFDB-7	2E8	7	8	3,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



2E8= Product Type Marking Code YM = Date Code Marking Y = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

Date Obde hey												
Year	2019		2020	2021		2022	2023		2024	2025		2026
Code	G		Н			J	K		L	М		Ν
	-			-		-						
Month	lan	Feb	Mar	Anr	May	lun	lul	Διια	Sen		Nov	Dec
Month Code	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec



## Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	Vсво	-20	
Collector-Emitter Voltage	Vceo	-20	V
Emitter-Base Voltage	Vebo	-7	
Peak Pulse Current	Ісм	-8	٨
Continuous Collector Current	lc	-6	A

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)	Π-	0.69	W
	(Note 6)	PD	1.25	vv
Thermal Desistance, Junction to Ambient	(Note 5)	D	180	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	R <sub>θJA</sub>	100	C/VV
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

## ESD Ratings (Note 7)

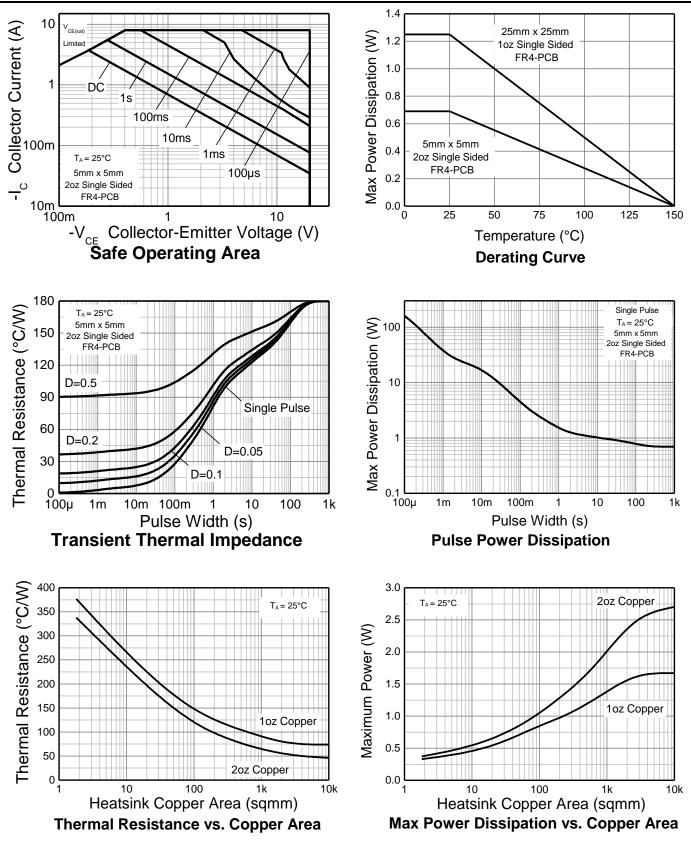
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 5. For a device mounted with the exposed collector on 5mm x 5mm 2oz copper on single sided FR4 PCB; device is measured under still air conditions whilst operating in the steady state.

6. Same as Note (5) except the exposed collector pad is mounted on 25mm x 25mm 1oz copper.
7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



## Thermal Characteristics and Derating Information





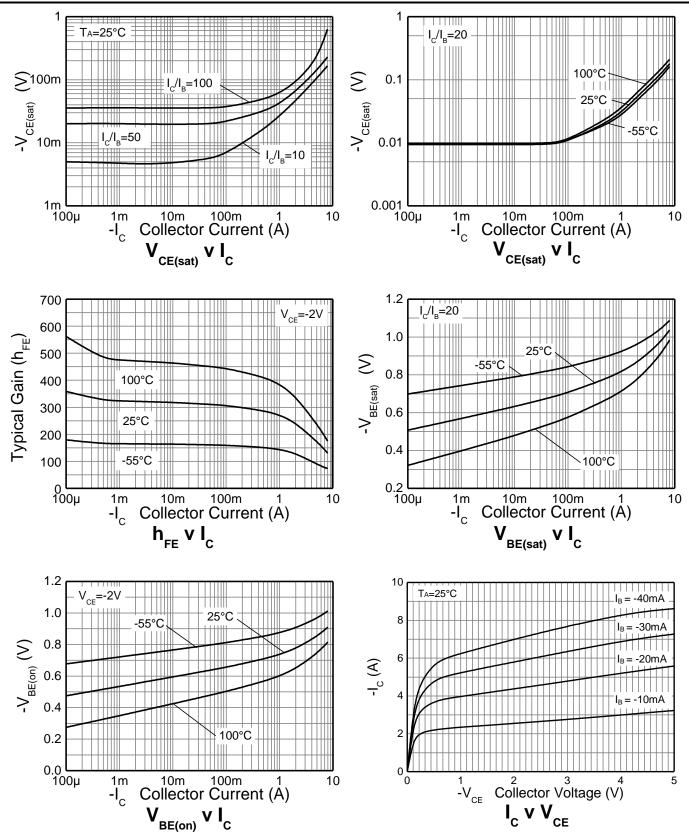
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	ВУсво	-20	_	_	V	Ic = -100μA
Collector-Emitter Breakdown Voltage (Note 8)	BVCEO	-20			V	Ic = -10mA
Emitter-Base Breakdown Voltage	BVEBO	-7			V	I <sub>E</sub> = -100μA
Collector Cutoff Current	Ісво	—	—	-100	nA	V <sub>CB</sub> = -16V
Emitter Cutoff Current	IEBO	—	_	-100	nA	$V_{EB} = -6V$
Collector Emitter Cutoff Current	ICES	—		-100	nA	Vces = -16V
		200	345	_		$I_{C} = -500 \text{mA}, V_{CE} = -2 \text{V}$
		200	320	_		$I_{C} = -1A, V_{CE} = -2V$
Static Forward Current Transfer Ratio (Note 8)	hfe	190	275	—	—	$I_{C} = -2A, V_{CE} = -2V$
		110	155	—		Ic = -6A, Vce = -2V
		_	-25	-40		Ic = -0.5A, I <sub>B</sub> = -50mA
		_	-50	-80		I <sub>C</sub> = -1A, I <sub>B</sub> = -50mA
		_	-80	-130		I <sub>C</sub> = -1A, I <sub>B</sub> = -10mA
Collector-Emitter Saturation Voltage (Note 8)	V <sub>CE(sat)</sub>	_	-135	-210	mV	$I_{\rm C} = -2A, I_{\rm B} = -20mA$
		_	-215	-325		Ic = -3A, I <sub>B</sub> = -30mA
		_	-150	-230		I <sub>C</sub> = -4A, I <sub>B</sub> = -400mA
		—	-235	-350		$I_{\rm C} = -6A, I_{\rm B} = -300 \text{mA}$
Base-Emitter Turn-On Voltage (Note 8)	VBE(on)	_	-0.76	-0.9	V	Ic = -2A, Vce = -2V
Base-Emitter Saturation Voltage (Note 8)	N/	—	-0.75	-0.9	V	Ic = -1A, I <sub>B</sub> = -10mA
base-Emilier Saturation Voltage (Note 6)	VBE(sat)	—	-1.03	-1.1	v	I <sub>C</sub> = -6A, I <sub>B</sub> = -300mA
Output Capacitance	Cobo	—	75	90	pF	V <sub>CB</sub> = -10V, f = 1MHz
Transition Frequency	fт	_	140	_	MHz	V <sub>CE</sub> = -10V, I <sub>C</sub> = -100mA, f = 100MHz
Delay Time	td	—	15	_		
Rise Time	tr	_	32	—		
Turn-On Time	t <sub>on</sub>	_	47	—		Vcc = -9V, Ic = -2A
Storage Time	ts	_	215		ns	$I_{B1} = -I_{B2} = -0.1A$
Fall Time	tf	—	47	—		
Turn-Off Time	t <sub>off</sub>	—	262			

Note: 8. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



### Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

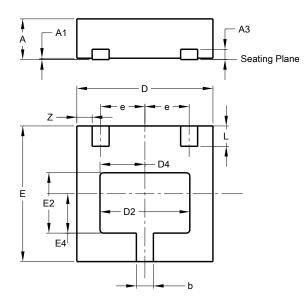




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-DFN2020-3 (Type B)

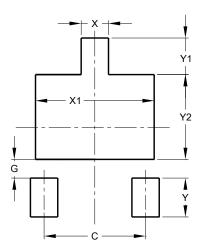


U-DFN2020-3 (Type B)					
Dim	Min	Max	Тур		
Α	0.57	0.63	0.60		
A1	0.00	0.05	0.02		
A3			0.152		
b	0.20	0.30	0.25		
D	1.950	2.075	2.00		
D2	1.22	1.42	1.32		
D4	0.56	0.76	0.66		
E	1.950	2.075	2.00		
E2	0.79	0.99	0.89		
E4	0.48	0.68	0.58		
е			0.65		
L	0.25	0.35	0.30		
Z		_	0.225		
All	Dimensi	ions in r	nm		

## Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-DFN2020-3 (Type B)



Dimensions	Value
Dimensions	(in mm)
С	1.300
G	0.240
Х	0.350
X1	1.520
Y	0.500
Y1	0.470
Y2	1.090



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